



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT
NPN General Purpose Transistor
 VOLTAGE 45 Volts CURRENT 0.1 Ampere

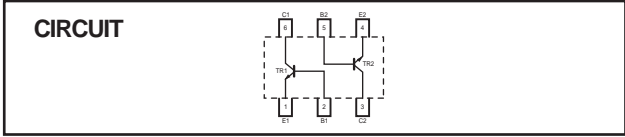
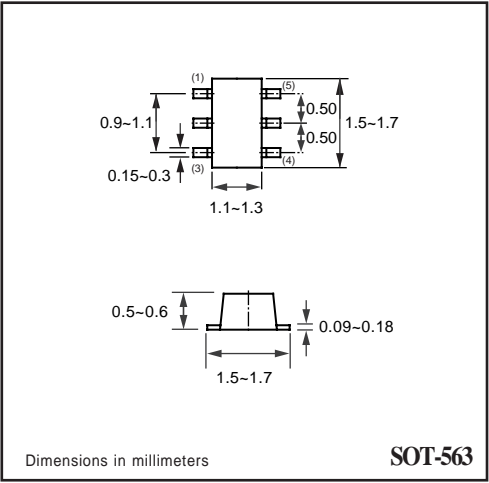
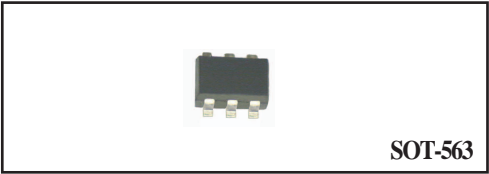
CHT847BVG

APPLICATION
 * AF input stages and driver applicationon equipment.
 * Other general purpose applications.

FEATURE
 * Small surface mounting type. (SOT-563)
 * High current gain.
 * Suitable for high packing density.
 * Low collector-emitter saturation.
 * High saturation current capability.

CONSTRUCTION
 * Two NPN transistors in one package.

MARKING
 * V3



LIMITING VALUES
 In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS		UNIT
V_{CBO}	collector-base voltage	open emitter	50	V
V_{CEO}	collector-emitter voltage	open base	45	V
V_{EBO}	emitter-base voltage	open collector	6	V
I_C	collector current (DC)		0.1	A
P_C	Collector power dissipation		150	mW
T_{stg}	storage temperature		-55~+150	°C
T_j	junction temperature		+150	°C

Note
 1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHT847BVGP)

THERMAL CHARACTERISTICS CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	Typ.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	-	-	15	nA
		$I_C = 0; V_{CB} = 30\text{ V}; T_A = 150\text{ }^{\circ}\text{C}$	-	-	5	μA
BV_{CBO}	collector-base breakdown voltage	$I_C = 50\text{ }\mu\text{A}$	50	-	-	V
BV_{CEO}	collector-emitter breakdown voltage	$I_C = 1\text{ mA}$	45	-	-	V
BV_{EBO}	emitter-base breakdown voltage	$I_E = 50\text{ }\mu\text{A}$	6	-	-	V
h_{FE}	DC current transfer ratio	$V_{CE}/I_C = 5\text{V}/2\text{ mA}$	200	-	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	100	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	-	-	300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	700	-	mV
C_{ib}	emitter input capacitance	$I_C = 0; V_{CB} = 0.5\text{ V}; f = 1\text{ MHz}$	-	8	-	pF
C_{ob}	collector output capacitance	$I_E = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	-	3	-	pF
f_T	transition frequency	$I_E = -20\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	-	200	-	MHz

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

RATING CHARACTERISTIC CURVES (CHT847BVGP)

fig1. Grounded emitter output characteristics

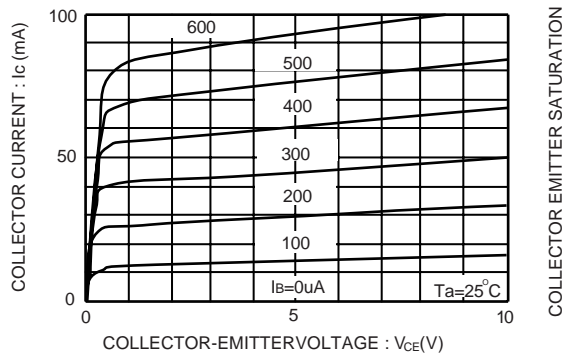
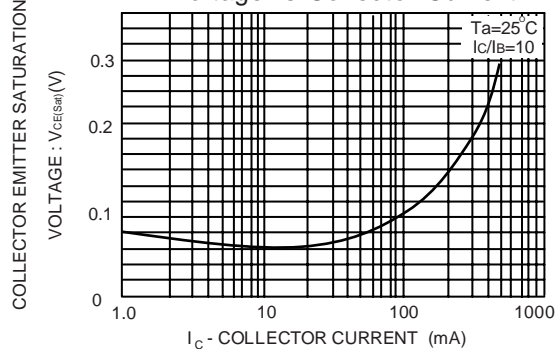


fig2. Collector-Emitter Saturation Voltage vs Collector Current



RATING CHARACTERISTIC CURVES (CHT847BVGP)

fig3.DC current gain VS. collector current (1)

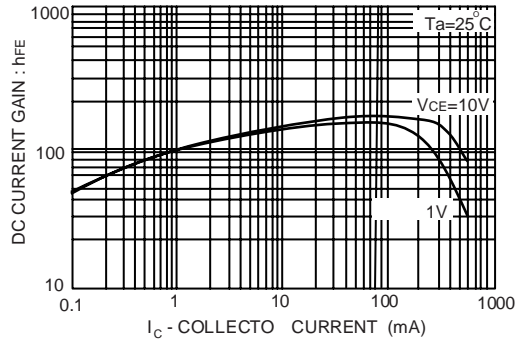


fig4.DC current gain VS. collector current (2)

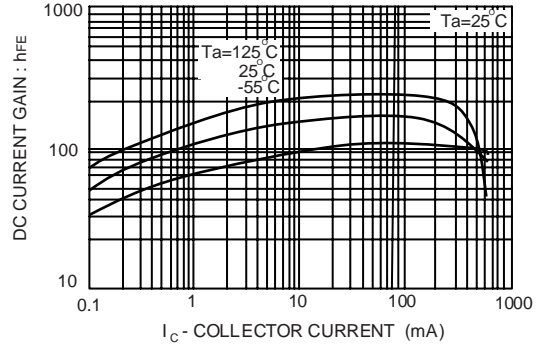


fig5.AC current gain VS. collector current

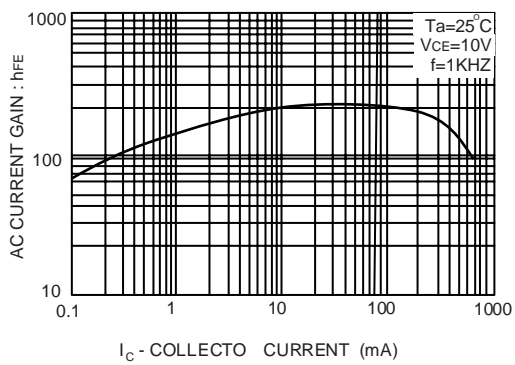


fig6.Base-emitter saturation voltage VS. collector current

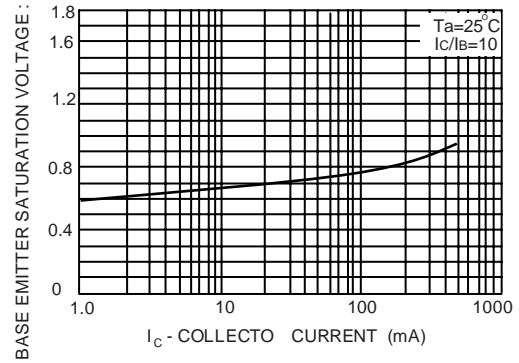


fig7.Grounded emitter propagation characteristics

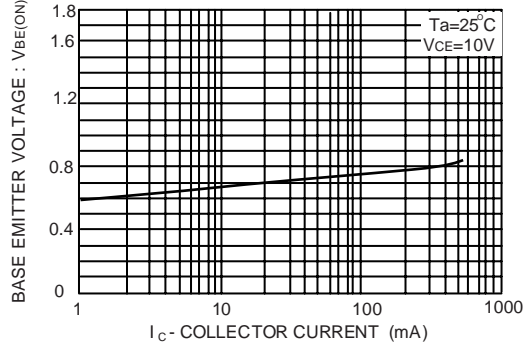
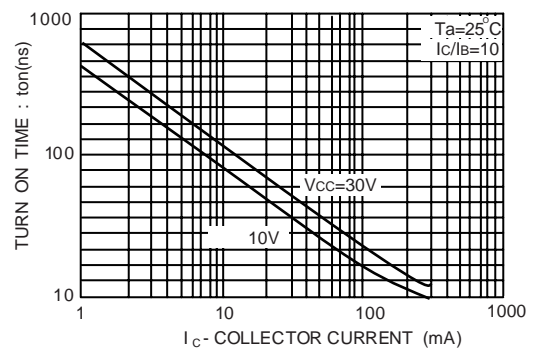


fig8.Turn-on time VS. collector current



RATING CHARACTERISTIC CURVES (CHT847BVGP)

fig9. Rise time VS. collector current

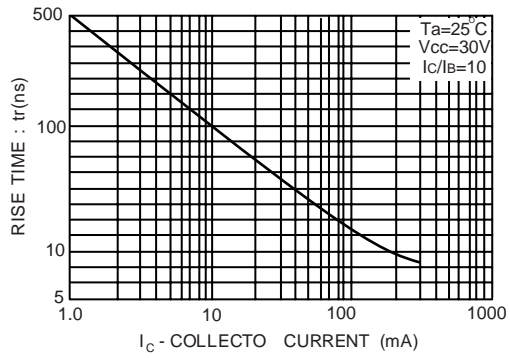


fig10. Fall time VS. collector current

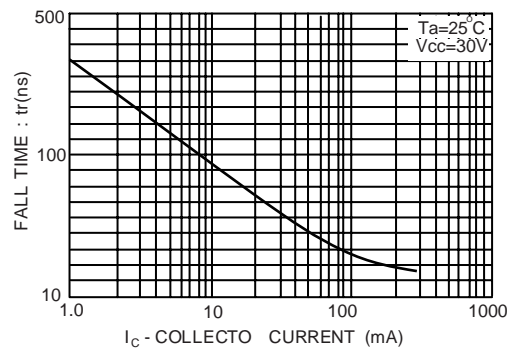


fig11. Input / output capacitance VS. voltage

